

# Low-Voltage Single SPDT Analog Switch

### DESCRIPTION

The DG9411 is a single-pole/double-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed ( $t_{ON}$ : 9 ns,  $t_{OFF}$ : 5 ns), low on-resistance ( $r_{DS(on)}$ : 7  $\Omega$ ) and small physical size (SC70), the DG9411 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG9411 is built on Vishay Siliconix's low voltage JI2 process. An epitaxial layer prevents latchup. Break-before - make is guaranteed for DG9411.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

### FEATURES

- Low voltage operation (2.25 V to 5.5 V)
- Low on-resistance  $r_{DS(on)}$ : 7  $\Omega$
- Fast switching t<sub>ON</sub>: 9 ns, t<sub>OFF</sub>: 5 ns
- Low charge injection Q<sub>INJ</sub>: 5 pC
- Low power consumption
- TTL/CMOS compatible
- 6-Pin SC70 package

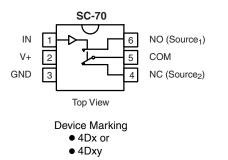
#### BENEFITS

- Reduced power consumption
- Simple logic interface
- High accuracy
- Reduce board space

#### **APPLICATIONS**

- Cellular phones
- Communication systems
- Portable test equipment
- · Battery operated systems
- Sample and hold circuits

#### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABL	E	
Logic	NC	NO
0	ON	OFF
1	OFF	ON

 $\begin{array}{l} \mbox{Logic "0"} \leq 0.8 \ \mbox{V} \\ \mbox{Logic "1"} \geq 2.4 \ \mbox{V} \end{array}$ 

ORDERING INFORMATION						
Temp Range	Temp Range Package Part Number					
- 40 to 85 °C	SC70-6	DG9411DL-T1 DG9411DL-T1-E3				

\* Pb containing terminations are not RoHS compliant, exemptions may apply.



COMPLIANT



ABSOLUTE MAXIMUM RATINGS						
Parameter	Limit	Unit				
Reference V+ to GND	ce V+ to GND - 0.3 to + 6					
IN, COM, NC, NO <sup>a</sup>		- 0.3 to (V+ + 0.3)	- V			
Continuous Current (Any Terminal)		± 50	mA			
Peak Current (Pulsed at 1 ms, 10 % du	ty cycle)	± 200	IIIA			
Storage Temperature		- 65 to 150	°C			
Power Dissipation (Packages) <sup>b</sup>	6-Pin SC70 <sup>c</sup>	250	mW			

Notes:

a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC Board. c. Derate 3.1 mW/°C above 70 °C.

SPECIFICATIONS V+ = 2.5 V										
		Test Conditions Unless Otherwise Specified V+ = 2.5 V, ± 10 %		Limits - 40 to 85 °C		°C				
Parameter	Symbol	$V_{\rm IN} = 0.4 \text{ or } 2.0 \text{ V}^{\rm e}$	Temp <sup>a</sup>	Min <sup>b</sup>	Тур <sup>с</sup>	Max <sup>b</sup>	Unit			
Analog Switch										
Analog Signal Range <sup>d</sup>	V <sub>NO</sub> , V <sub>NC</sub> V <sub>COM</sub>		Full	0		V+	V			
Drain-Source On-Resistance	r <sub>DS(on)</sub>	V+ = 2.25 V, V <sub>D</sub> = 1.0 V, I <sub>S</sub> = 10 mA	Room Full <sup>d</sup>		26 29	35 40	0			
r <sub>DS(on)</sub> Flatness <sup>d</sup>	r <sub>DS(on)</sub> Flatness	V+ = 2.5 V	Room		10		Ω			
Switch Off	I <sub>S(off)</sub>	V+ = 2.75 V, V <sub>S</sub> = 0.5 V/1.5 V, V <sub>D</sub> = 1.5 V/0.5 V	Room Full <sup>d</sup>	- 250 - 3.0		250 3.0	pA nA			
Leakage Current <sup>®</sup>	I <sub>D(off)</sub>		Room Full <sup>d</sup>	- 250 - 3.0		250 3.0	pA nA			
Channel-On Leakage Current <sup>f</sup>	I <sub>D(on)</sub>	V+ = 2.75 V, V <sub>S</sub> = V <sub>D</sub> = 0.5 V/1.5 V	Room Full <sup>d</sup>	- 250 - 3.0		250 3.0	pA nA			
Digital Control					-					
Input High Voltage	V <sub>INH</sub>		Full	2			v			
Input Low Voltage	V <sub>INL</sub>		Full			0.4	v			
Input Capacitance <sup>d</sup>	C <sub>in</sub>		Full		3		pF			
Input Current	$I_{\rm INL}$ or $I_{\rm INH}$	V <sub>IN</sub> = 0 or V+	Full	- 1		1	μΑ			
Dynamic Characteristics					-					
Turn-On Time	t <sub>ON</sub>	$V_D$ or $V_S$ = 1.5 V, $R_L$ = 300 Ω, $C_L$ = 35 pF	Room Full <sup>d</sup>		16	40 45				
Turn-Off Time	t <sub>OFF</sub>	$V_D$ of $V_S = 1.5$ V, $H_L = 300$ S2, $U_L = 35$ pr Figures 1 and 2	Room Full		7	23 28	ns			
Break-Before-Make Time	t <sub>d</sub>		Room <sup>d</sup>	1	12					
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	$C_L$ = 1 nF, $V_{GEN}$ = 0 V, $V_S$ = 0 V, $R_{GEN}$ = 0 $\Omega,$ Figure 3	Room		5	10	рС			
Off-Isolation <sup>d</sup>	OIRR	$R_{I} = 50 $ Ω, $C_{I} = 5 $ pF, f = 1 MHz	Room		- 73		dB			
Crosstalk <sup>d</sup>	X <sub>TALK</sub>		Room		- 70		uВ			
Source-Off Capacitance <sup>d</sup>	C <sub>S(off)</sub>		Room		7					
Channel-On Capacitance <sup>d</sup>	C <sub>D(on)</sub>	$V_{IN} = 0$ or V+, f = 1 MHz	Room		20		pF			
Drain-to-Source Capacitanced	C <sub>DS(off)</sub>		Room		20					
Power Supply										
Power Supply Range	V+			2.25		2.75	V			
Power Supply Current <sup>d</sup>	l+	$V_{IN} = 0 \text{ or } V+$			0.01	1.0	μA			
Power Consumption	P <sub>C</sub>					0.3	μW			



SPECIFICATIONS V+ = 3 V								
		Test Conditions Unless Otherwise Specified V+ = 3 V, ± 10 %			Limits - 40 to 85 °C			
Parameter	Symbol	$V_{IN} = 0.4$ or 2.0 V <sup>e</sup>	Temp <sup>a</sup>	Min <sup>b</sup>	Тур <sup>с</sup>	Max <sup>b</sup>	Unit	
Analog Switch								
Analog Signal Range <sup>d</sup>	$V_{ m NO}, V_{ m NC}$ $V_{ m COM}$		Full	0		V+	v	
Drain-Source On-Resistance <sup>d</sup>	r <sub>DS(on)</sub>	V+ = 2.7 V, V <sub>D</sub> = 1.5 V, I <sub>S</sub> = 10 mA	Room Full		15 19	25 30	Ω	
r <sub>DS(on)</sub> Flatness <sup>d</sup>	r <sub>DS(on)</sub> Flatness	$V_{S}$ = 0 to V+, I <sub>S</sub> = 10 mA	Room		7.5		32	
Switch Off	I <sub>S(off)</sub>	V+ = 3.3 V, V <sub>S</sub> = 1 V/3 V, V <sub>D</sub> = 3 V/1 V	Room Full	- 500 - 4.0		500 4.0	pA nA	
Leakage Current <sup>†</sup>	I <sub>D(off)</sub>		Room Full	- 500 - 4.0		500 4.0	pA nA	
Channel-On Leakage Current <sup>f</sup>	I <sub>D(on)</sub>	V+ = 3.3 V, V <sub>S</sub> = V <sub>D</sub> = 1 V/3 V	Room Full	- 500 - 4.0		500 4.0	pA nA	
Digital Control			•					
Input High Voltage	V <sub>INH</sub>		Full	2			v	
Input Low Voltage	V <sub>INL</sub>		Full			0.8	v	
Input Capacitance <sup>d</sup>	C <sub>in</sub>		Full		3		pF	
Input Current	I <sub>INL</sub> or I <sub>INH</sub>	V <sub>IN</sub> = 0 or V+	Full	- 1		1	μA	
Dynamic Characteristics								
Turn-On Time <sup>d</sup>	t <sub>ON</sub>	$V_D$ or $V_S$ = 2.0 V, $R_L$ = 300 $\Omega$ , $C_L$ = 35 pF	Room Full		12	15 20		
Turn-Off Time <sup>d</sup>	t <sub>OFF</sub>	$V_D$ or $V_S = 2.0$ V, $H_L = 300 \Omega_2$ , $G_L = 35 \text{ pr}$ Figures1 and 2	Room Full		6	8 10	ns	
Break-Before-Make Time <sup>d</sup>	t <sub>d</sub>		Room	1	7			
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	$C_{L}$ = 1 nF, $V_{GEN}$ = 0 V, $V_{S}$ = 0 V, $R_{GEN}$ = 0 $\Omega,$ Figure 3	Room		5	10	рС	
Off-Isolation <sup>d</sup>	OIRR	$R_1 = 50 \Omega_2 C_1 = 5 pF, f = 1 MHz$	Room		- 73		dB	
Crosstalk <sup>d</sup>	X <sub>TALK</sub>	11 = 30.32, 01 = 3.01, 1 = 1.10112	Room		- 70		uВ	
Source-Off Capacitance <sup>d</sup>	C <sub>S(off)</sub>		Room		7			
Channel-On Capacitance <sup>d</sup>	C <sub>D(on)</sub>	$V_{IN} = 0$ or V+, f = 1 MHz	Room		20		рF	
Drain-to-Source Capacitance <sup>d</sup>	C <sub>DS(off)</sub>		Room		20			
Power Supply			·					
Power Supply Range	V+			2.7		3.3	V	
Power Supply Current	$V_{\rm eff} = 0$ or $V_{\rm eff}$				0.01	1.0	μΑ	
Power Consumption	P <sub>C</sub>					0.4	μW	



SPECIFICATIONS V-	+ = 5 V		-				-
		Test Conditions Unless Otherwise Specified $V+ = 5 V, \pm 10 \%$		Limits - 40 to 85 °C			-
Parameter	Symbol	$V_{IN} = 0.8 \text{ or } 2.4 \text{ V}^{e}$	Temp <sup>a</sup>	Min <sup>b</sup>	Тур <sup>с</sup>	Max <sup>b</sup>	Unit
Analog Switch				1			
Analog Signal Range <sup>d</sup>	V <sub>NO</sub> , V <sub>NC</sub> V <sub>COM</sub>		Full	0		V+	V
Drain-Source On-Resistance	r <sub>DS(on)</sub>	V+ = 4.5 V, V <sub>D</sub> = 3 V, I <sub>S</sub> = 10 mA	Room Full		7 10	12 16	Ω
r <sub>DS(on)</sub> Flatness <sup>d</sup>	r <sub>DS(on)</sub> Flatness	V+ = 2.5 V	Room		2		52
Switch Off	I <sub>S(off)</sub>	V+ = 5.5 V, V <sub>S</sub> = 1 V/4.5 V, V <sub>D</sub> = 4.5 V/1 V	Room Full	- 1.0 - 4.0		1.0 4.0	
Leakage Current	I <sub>D(off)</sub>	v+ = 0.0 v, vg = 1 v/4.0 v, vD = 4.0 v/1 v	Room Full	- 1.0 - 4.0		1.0 4.0	nA
Channel-On Leakage Current	I <sub>D(on)</sub>	V+ = 5.5 V, V <sub>S</sub> = V <sub>D</sub> = 1 V/4.5 V	Room Full	- 1.0 - 3.0		1.0 4.5	
Digital Control							
Input High Voltage	V <sub>INH</sub>		Full	2.4			v
Input Low Voltage	V <sub>INL</sub>		Full			0.8	v
Input Capacitance	C <sub>in</sub>		Full		3		pF
Input Current	I <sub>INL</sub> or I <sub>INH</sub>	V <sub>IN</sub> = 0 or V+	Full	- 1		1	μΑ
Dynamic Characteristics							
Turn-On Time <sup>d</sup>	t <sub>ON</sub>	V <sub>D</sub> or V <sub>S</sub> = 3 V, R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF	Room Full		9	11 15	
Turn-Off Time <sup>d</sup>	t <sub>OFF</sub>	$v_D$ of $v_S = 3 v_1 H_L = 300 32, U_L = 35 pF$ Figure 1 and 2	Room Full		5	7 9	ns
Break-Before-Make Time <sup>d</sup>	t <sub>d</sub>		Room	1	4		
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	$C_L$ = 1 nF, $V_S$ = 0 V, $V_{GEN}$ = 0 V, $R_{GEN}$ = 0 $\Omega$ , Figure 3	Room		5	10	рС
Off-Isolation <sup>d</sup>	OIRR	$R_1 = 50 \Omega_2 C_1 = 5 pF_1 f = 1 MHz$	Room		- 73		-10
Crosstalk <sup>d</sup>	X <sub>TALK</sub>	$H_{L} = 50.52, G_{L} = 5 \text{ pr}, T = T \text{ MHz}$	Room		- 70		dB
Source-Off Capacitance <sup>d</sup>	C <sub>S(off)</sub>		Room		7		
Channel-On Capacitance <sup>d</sup>	C <sub>D(on)</sub>	$V_{IN} = 0$ or V+, f = 1 MHz	Room		20		pF
Drain-to-Source Capacitance <sup>d</sup>	C <sub>DS(off)</sub>		Room		20		р
Power Supply						•	
Power Supply Range	V+			4.5		5.5	V
Power Supply Current	l+	V <sub>IN</sub> = 0 or V+			0.01	1.0	μA
Power Consumption	P <sub>C</sub>					0.6	μW

Notes:

a. Room = 25  $^{\circ}$ C, Full = as determined by the operating suffix.

b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.

c. Typical values are for design aid only, not guaranteed nor subject to production testing.

d. Guarantee by design, nor subjected to production test.

e.  $V_{IN}$  = input voltage to perform proper function.

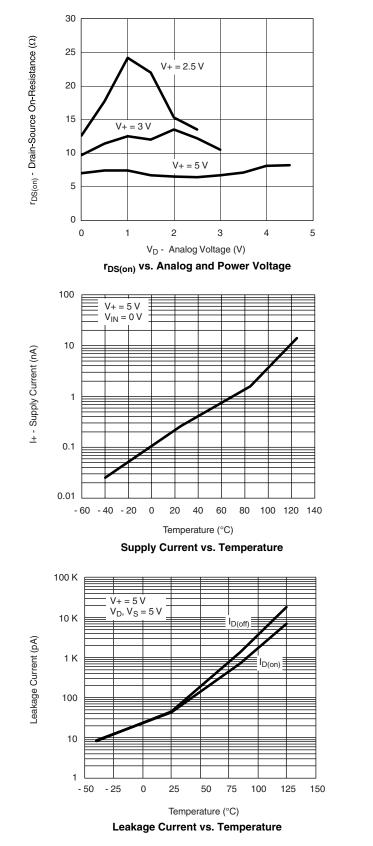
f. Guaranteed by 5 V leakage testing, not production tested.

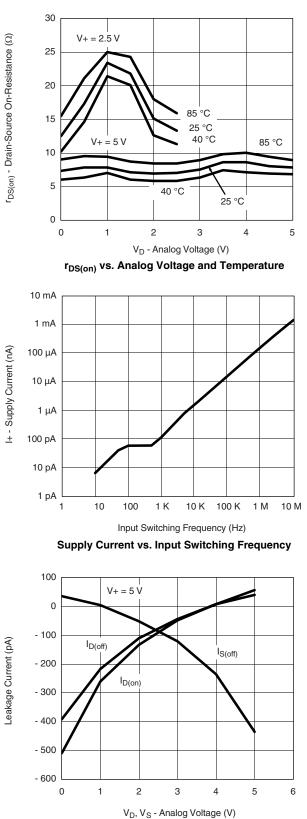
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



# DG9411 Vishay Siliconix

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

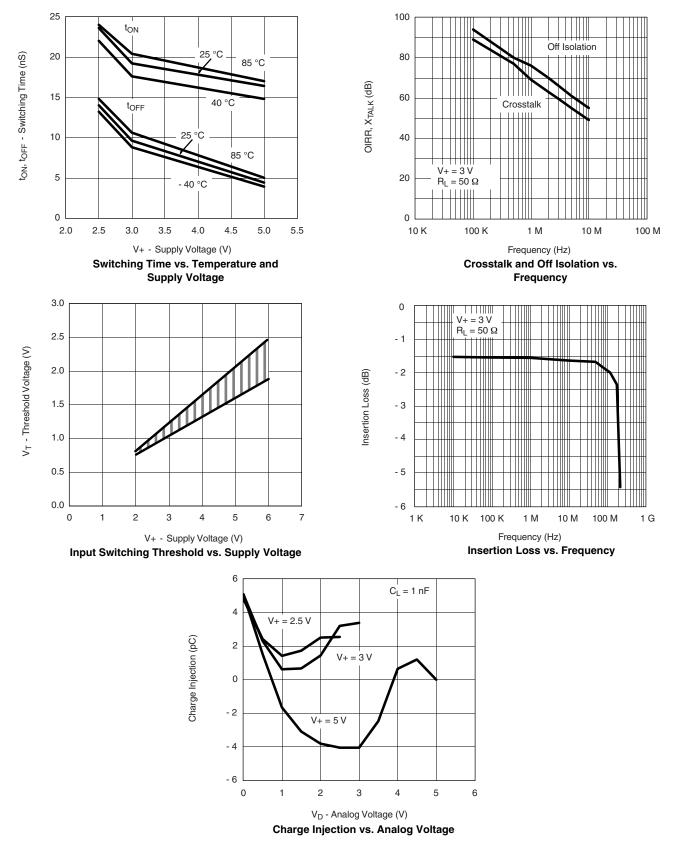




Leakage vs. Analog Voltage



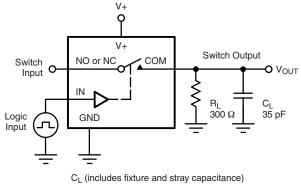
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



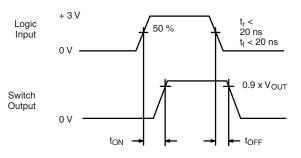


## DG9411 Vishay Siliconix

### **TEST CIRCUITS**

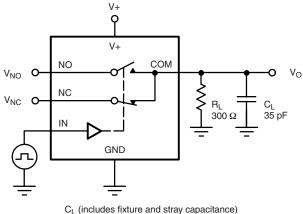






Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

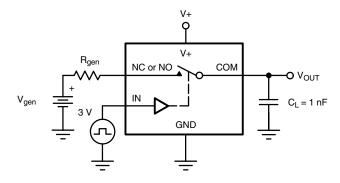


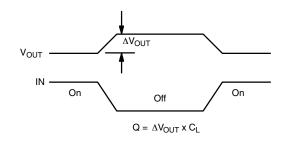


Logic 3 VInput 0 V  $V_{NC} = V_{NO}$   $V_{O}$ Switch 0 V  $V_{D}$   $V_{D}$  $V_{D}$ 

includes inclure and stray capacitance)







IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection

## DG9411

Vishay Siliconix



### **TEST CIRCUITS**

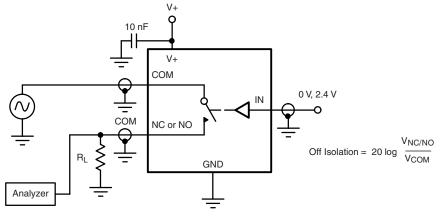


Figure 4. Off-Isolation

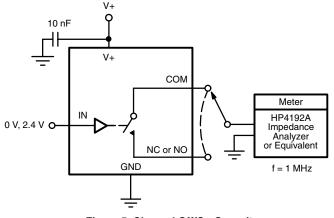


Figure 5. Channel Off/On Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?71347.



# Package Information Vishay Siliconix

### SC-70: 6-LEADS





	MIL	LIMET	ERS	INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.90	-	1.10	0.035	-	0.043	
A <sub>1</sub>	-	-	0.10	-	-	0.004	
A <sub>2</sub>	0.80	-	1.00	0.031	-	0.039	
b	0.15	-	0.30	0.006	-	0.012	
С	0.10	-	0.25	0.004	-	0.010	
D	1.80	2.00	2.20	0.071	0.079	0.087	
Е	1.80	2.10	2.40	0.071	0.083	0.094	
E <sub>1</sub>	1.15	1.25	1.35	0.045	0.049	0.053	
е		0.65BSC			0.026BSC	;	
e <sub>1</sub>	1.20	1.30	1.40	0.047	0.051	0.055	
L	0.10	0.20	0.30	0.004	0.008	0.012	
٩	7°Nom 7°Nom						
ECN: S-03946—Rev. B, 09-Jul-01 DWG: 5550							



Vishay

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